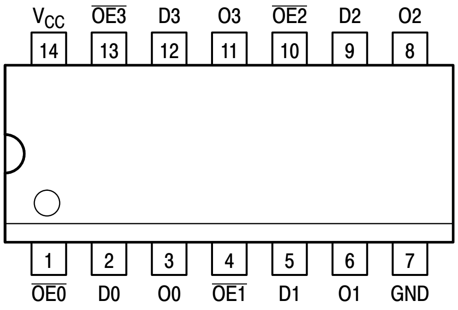


Figure 1. 14−Lead Pinout (Top View)

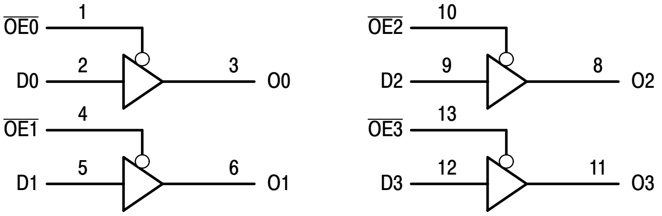


Figure 2. Logic Diagram

PIN NAMES

Pins	Function
$\overline{\text{OEn}}$	Output Enable Inputs
Dn	Data Inputs
On	3−State Outputs

FUNCTION TABLE

INPUTS		OUTPUTS
$\overline{\text{OEn}}$	Dn	On
L	L	L
L	H	H
H	X	Z

H = High Voltage Level; L = Low Voltage Level; Z = High Impedance State; X = High or Low Voltage Level and Transitions Are Acceptable, for I_{CC} reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	–0.5 to +7.0	V
V_{in}	DC Input Voltage	–0.5 to +7.0	V
V_{out}	DC Output Voltage	–0.5 to V_{CC} +0.5	V
I_{IK}	Input Diode Current	−20	mA
I_{OK}	Output Diode Current	±20	mA
I_{out}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±50	mA
P_D	Power Dissipation	180	mW
T_{stg}	Storage Temperature	–65 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	3.6	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	−40	+85	°C
$\Delta t/\Delta V$	Input Rise and Fall Time	0	100	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} V	T_A = 25°C			T_A = − 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V_{IL}	Low−Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V_{OH}	High−Level Output Voltage (V_{in} = V_{IH} or V_{IL})	I_{OH} = −50μA I_{OH} = −50μA I_{OH} = −4mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V_{OL}	Low−Level Output Voltage (V_{in} = V_{IH} or V_{IL})	I_{OL} = 50μA I_{OL} = 50μA I_{OL} = 4mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I_{in}	Input Leakage Current	V_{in} = 5.5V or GND	3.6			±0.1		±1.0	μA
I_{OZ}	Maximum Three−State Leakage Current	V_{in} = V_{IL} or V_{IH} V_{out} = V_{CC} or GND	3.6			±0.25		±2.5	μA
I_{CC}	Quiescent Supply Current	V_{in} = V_{CC} or GND	3.6			4.0		40.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T_A = 25°C			T_A = − 40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay Input to Output	V_{CC} = 2.7V C_L = 15pF C_L = 50pF		5.8 8.3	10.1 13.6	1.0 1.0	13.5 17.0	ns
		V_{CC} = 3.3 ± 0.3V C_L = 15pF C_L = 50pF		4.4 6.9	6.2 9.7	1.0 1.0	8.5 12.0	
t_{PZL}, t_{PZH}	Output Enable Time $\overline{OE}$ to O	V_{CC} = 2.7V C_L = 15pF R_L =1kΩ C_L = 50pF		5.3 7.8	9.3 12.8	1.0 1.0	12.5 16.0	ns
		V_{CC} = 3.3 ± 0.3V C_L = 15pF R_L =1kΩ C_L = 50pF		4.0 6.5	5.6 9.1	1.0 1.0	7.5 11.0	
t_{PLZ}, t_{PHZ}	Output Disable Time $\overline{OE}$ to O	V_{CC} = 2.7V C_L = 50pF R_L =1kΩ		10.0	15.7	1.0	19.0	ns
		V_{CC} = 3.3 ± 0.3V C_L = 50pF R_L =1kΩ		8.3	11.2	1.0	13.0	
t_{OSHL} t_{OSLH}	Output−to−Output Skew (Note 1)	V_{CC} = 2.7V C_L = 50pF V_{CC} = 3.3 ±0.3V C_L = 50pF			1.5 1.5		1.5 1.5	ns

1. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH−to−LOW (t_{OSHL}) or LOW−to−HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	T_A = 25°C			T_A = − 40 to 85°C		Unit
		Min	Typ	Max	Min	Max	
C_{in}	Input Capacitance		4	10		10	pF
C_{out}	Maximum Three−State Output Capacitance		6				pF
C_{PD}	Power Dissipation Capacitance (Note 2)		14				pF

2. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$ (per bit). C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ns, $C_L = 50$pF, $V_{CC} = 3.3$V, Measured in SOIC Package)

Symbol	Characteristic	$T_A = 25°C$		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.5	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.3	−0.5	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

ORDERING INFORMATION

Device	Package	Shipping†
MC74LVX125D	SOIC−14	55 Units / Rail
MC74LVX125DG	SOIC−14 (Pb−Free)	55 Units / Rail
MC74LVX125DR2	SOIC−14	2500 Tape & Reel
MC74LVX125DR2G	SOIC−14 (Pb−Free)	2500 Tape & Reel
MC74LVX125DT	TSSOP−14*	96 Units / Rail
MC74LVX125DTR2	TSSOP−14*	2500 Tape & Reel
MC74LVX125M	SOEIAJ−14	2000 Tape & Reel
MC74LVX125MEL	SOEIAJ−14	2000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb−Free.

SWITCHING WAVEFORMS

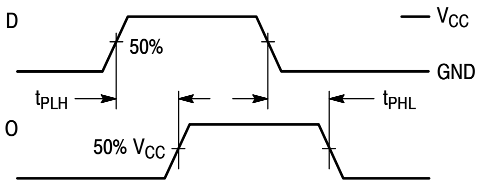


Figure 3.

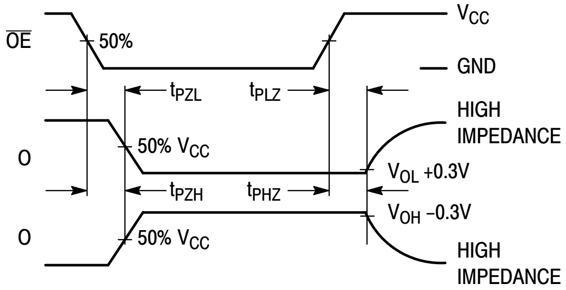
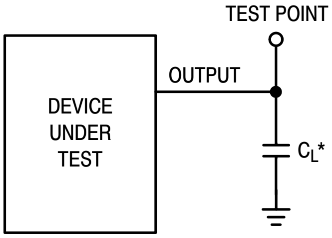


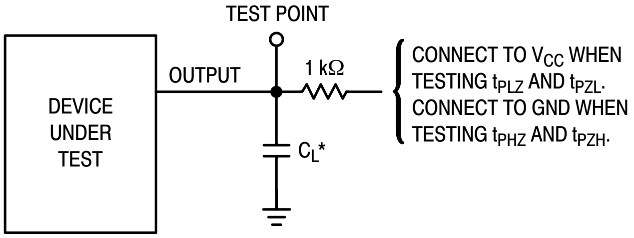
Figure 4.

TEST CIRCUITS



*Includes all probe and jig capacitance

Figure 5. Propagation Delay Test Circuit



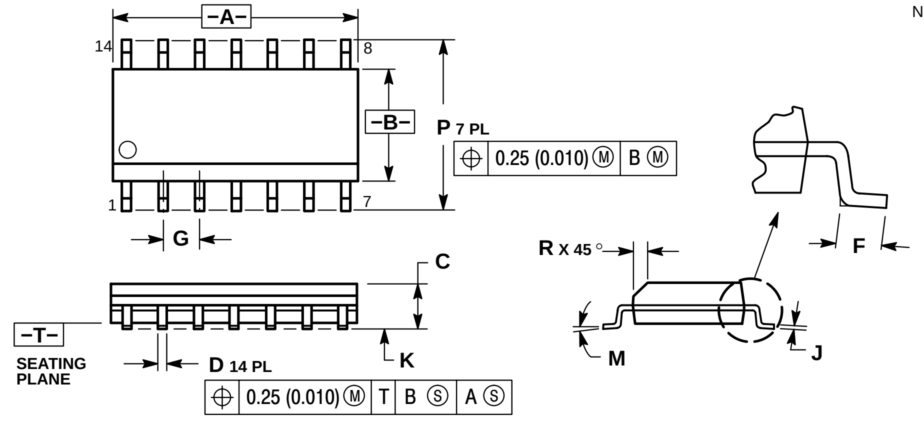
*Includes all probe and jig capacitance

Figure 6. Three−State Test Circuit

PACKAGE DIMENSIONS

SOIC−14
D SUFFIX

CASE 751A−03
ISSUE G

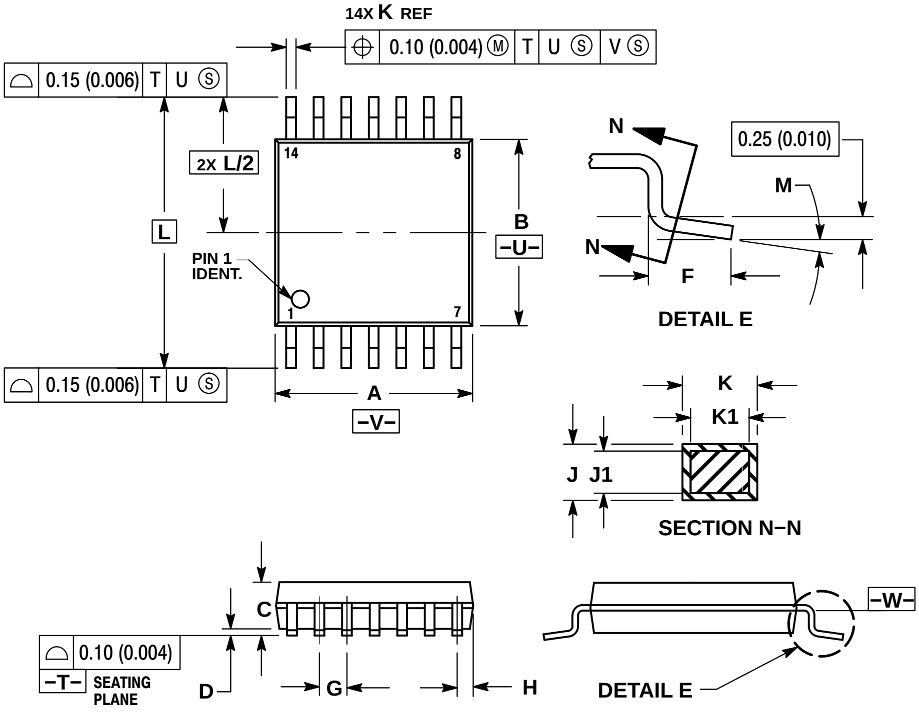


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

TSSOP−14
DT SUFFIX

CASE 948G−01
ISSUE O

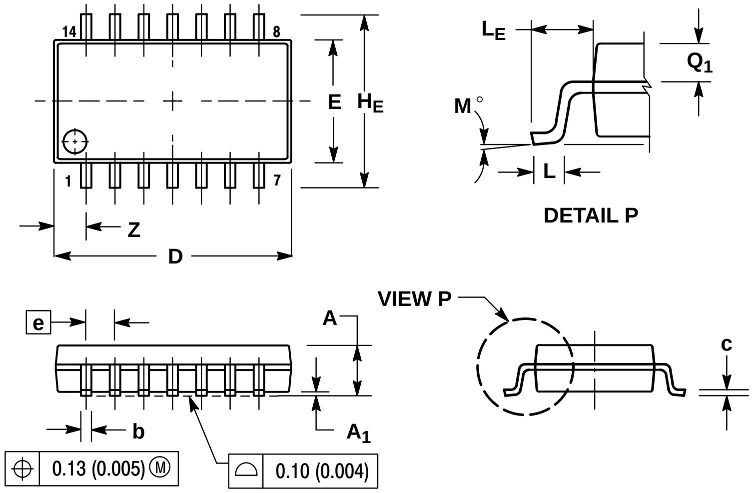


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

PACKAGE DIMENSIONS

SOEIAJ−14
M SUFFIX
CASE 965−01
ISSUE O



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	**MIN**	**MAX**	**MIN**	**MAX**
A	−−−	2.05	−−−	0.081
A_1	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H_E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
L_E	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z	−−−	1.42	−−−	0.056

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